Appl. No. 10/071,748 Amdt. dated September 2, 2004 Amendment under 37 CFR 1.116 Expedited Procedure Examining Group

Listing of he Claims:

This listing reflects the current status of the claims in the application and replaces all prior versions, and listings:

1. (Previously Presented) A process for producing a reaction bonded silicon carbide body, the process comprising:

combining about 0 wt% to about 35 wt% of a carbon source, about 40 wt% to about 90 wt% silicon carbide, about 0.01 wt% to about 15 wt% starch, and about 10 wt% to about 30 wt% liquid to form a ceramic slurry;

compacting the ceramic slurry into a green body; and exposing the green body to liquid silicon metal to produce a reaction bonded silicon carbide body.

- 2. (Original) A process as in claim 1, wherein the carbon source is selected from the group consisting of carbon black and colloidal graphite, and the silicon carbide comprises alpha silicon carbide grit.
- 3. (Previously Presented) A process as in claim 1, wherein the ceramic slurry includes about 0 wt% to about 20 wt% carbon black, and about 0 wt% to about 15 wt% colloidal graphite.
- 4. (Previously Presented) A process as in claim 1, wherein the the starch is selected from a group consisting of corn starch, potato starch, tapioca starch, and wheat starch.
- 5. (Previously Presented) A process as in claim 1, wherein the ceramic slurry includes about 0.01 wt% to about 5 wt% potato starch as the starch.
- 6. (Original) A process as in claim 1, further comprising heating the green body to a temperature of about 1400°C to about 1650°C during siliconization.

PATENT

Appl. No. 10/071,748

Amdt. dated September 2, 2004

Amendment under 37 CFR 1.116 Expedited Procedure

Examining Group

- 7. (Original) A process as in claim 1, wherein siliconization comprises exposing the green body to about 20 wt% to 150 wt% (based on green body weight) liquid silicon metal.
- 8. (Original) A process as in claim 1, wherein compacting the ceramic slurry comprises forcing the ceramic slurry into a porous mold with a pore size of about 2 microns to about 20 microns and applying pressure of about 70 psig to about 600 psig for about 10 seconds to about 240 seconds.
- 9. (Original) A process as in claim 1, further comprising agitating the ceramic slurry continuously at low shear for about 4 hours to about 15 hours under vacuum conditions.
- 10. (Original) A process as in claim 1, wherein combining further comprises mixing the ceramic slurry for about 10 minutes to about 60 minutes using a high shear, high intensity mixer.
- 11. (Original) A process as in claim 1, further comprising drying the green body in a conveyor drying oven at about 30 °C to about 200 °C for about 5 minutes to about 12 minutes.
- 12. (Original) A process as in claim 1, wherein the silicon carbide body comprises an armor torso.
 - 13-24. (Canceled)
- 25. (Previously Presented) A process as in claim 1, wherein the liquid is water.
- 26. (Previously Presented) A process for producing a reaction bonded silicon carbide body, the process comprising:

Appl. No. 10/071,748 Amdt. dated September 2, 2004 Amendment under 37 CFR 1.116 Expedited Procedure

Examining Group

forming a green body from a ceramic slurry comprising silicon carbide, about 0.01 wt% to about 15 wt% starch, and about 10 wt% to about 30 wt% water; and exposing the green body to liquid silicon metal to produce a reaction bonded silicon carbide body.

- 27. (Previously Presented) A process as in claim 26, wherein the green body is formed by compacting the ceramic slurry.
- 28. (Previously Presented) A process according to claim 27, wherein the compacting is accomplished through pressure cast molding.
- 29. (Previously Presented) A process according to claim 26, wherein the ceramic slurry comprises a carbon source.
- 30. (Previously Presented) A process according to claim 26, wherein the ceramic slurry comprises about 0 wt% to about 20 wt% carbon black, and about 0 wt% to about 15 wt% colloidal graphite.
- 31. (Previously Presented) A process according to claim 26, wherein the ceramic slurry comprises about 40 wt% to about 90 wt% alpha silicon carbide grit as the silicon carbide.
- 32. (Previously Presented) A process according to claim 26, wherein the ceramic slurry comprises about 0.01 wt% to about 5 wt% potato starch as the starch.